

HSC285

Silicon Schottky Barrier Diode for High frequency detection

REJ03G0011-0100Z Rev.1.00 Apr.16.2003

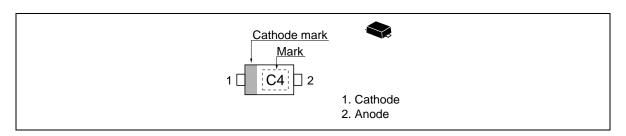
Features

- Low forward voltage, Low capacitance and High detection sensitivity.
- Ultra small Flat Package (UFP) is suitable for surface mount design.

Ordering Information

| Type No. | Laser Mark | Package Code |
|----------|------------|--------------|
| HSC285 | C4 | UFP |

Pin Arrangement



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Value | Unit |
|---------------------------|----------------|-------------|------|
| Reverse voltage | V_R | 2 | V |
| Average rectified current | I _o | 5 | mA |
| Junction temperature | Tj | 125 | °C |
| Storage temperature | Tstg | -55 to +125 | °C |

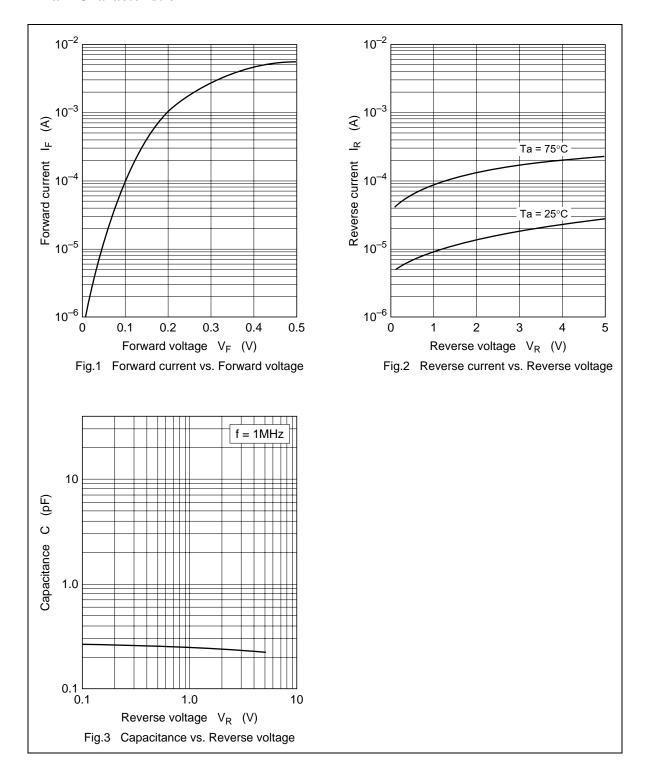
Electrical Characteristics

 $(Ta = 25^{\circ}C)$

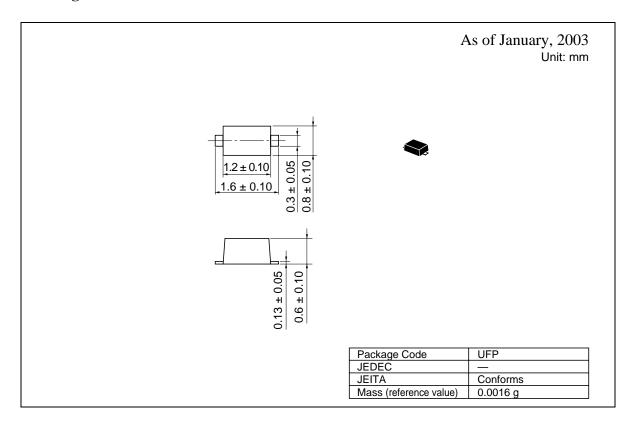
| Item | Symbol | Min | Тур | Max | Unit | Test Condition |
|-------------------|-----------------|-----|-----|------|-------------|--|
| Forward voltage | V _{F1} | _ | _ | 0.15 | V | I _F = 0.1 mA |
| | V _{F2} | _ | _ | 0.27 | | I _F = 1 mA |
| Capacitance | С | _ | 0.3 | _ | рF | V _R = 1 V, f = 1 MHz |
| ESD-Capability *1 | _ | 10 | _ | _ | V | C = 200 pF, $R_L = 0 \Omega$, Both forward and reverse direction 1 pulse. |

Note: 1. Failure criterion; $I_R > 100 \mu A$ at $V_R = 0.5 V$

Main Characteristic



Package Dimensions



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